



## Patent Number: 6,026,014

(45) Date of Patent: Feb. 15, 2006

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|------|---|-----------|--------|---------------------|-------------|
| [54] | NONVOLATILE SEMICONDUCTOR<br>MEMORY AND READ METHOD | 4,558,088 | 4/1/88 | Ong et al.          | 565,623     |
| [55] | Nonvolatile semiconductor<br>memory and read method | 4,561,091 | 4/1/88 | Mikolajewski et al. | 565,628     |
| [56] | Nonvolatile semiconductor<br>memory and read method | 4,562,040 | 4/1/88 | Baltes et al.       | 565,716     |
| [57] | Nonvolatile semiconductor<br>memory and read method | 4,562,478 | 4/1/88 | Takahashi et al.    | 565,743,344 |
- FOREIGN PATENT DOCUMENTS
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| [73] | Antigenes: Ethanol-LDL<br>Engineering Corp., Inc. of Japan;<br>Ethanol Development Engineering Co., Ltd.,<br>Osaka, Jpn. of Japan | 5-1401 | 1/1996 | Japan |
|------|---|--------|--------|-------|
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- ABSTRACT
- [57] In a nonvolatile semiconductor memory in which multiple-value information is stored in one memory cell by setting a value of threshold voltage of a transistor in accordance with threshold level with continuously changing the word-line level, the word-line level is advantageously provided to a highest level, and the access time is shortened in accordance with the data stored in each memory for reading data.
- U.S. PATENT DOCUMENTS
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| 4,558,070 | 20,180 | Feb. | 1983 | 565,685 |
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- 37 Cl. Int. 22, Division 82

